

REMARKS/ARGUMENTS

Claims 25, 26, 28, and 29 were rejected under 35 U.S.C. §102(e) as being anticipated by Fujishima et al., U.S. Patent No. 6,740,952. Reconsideration of the rejection is respectfully requested.

Independent claim 25 has been amended to provide for, “[a] field plate structure comprising: a first field plate; a second field plate disposed above and spaced from said first field plate; and a third field plate disposed above and spaced from said second field plate, said field plate structure being disposed over a resurf region.” Antecedent support for the amendment can be found in the specification in paragraph [0020], lines 1-3.

In regard to claim 25, the Examiner indicates that elements 9, FP1, and FP2, in Fig. 19, are equivalent to the first field plate, the second field, and the third field plate, respectively, claimed in claim 25. However, Fig. 19 nowhere shows, discloses, or suggests a resurf region over which the field plate structure allegedly shown in Fig. 19 is disposed.

Since claims 26, 28, and 29 are directly or indirectly dependent upon independent claim 25 they are allowable over Fujishima et al. for the same reasons recited above with respect to the allowability of independent claim 25 over Fujishima et al.

Claims 1-13, and 24 were rejected under 35 U.S.C. §103(a) as being unpatentable over Fujishima et al. in view of Van Zant and Ghandhi. Reconsideration of the rejection is respectfully requested.

Independent claim 1 has been amended, in part, to provide for, “[a] semiconductor device comprising: ... a resurf region of said first conductivity formed in said epitaxially formed semiconductor layer, said resurf region being formed over at least a portion of said drift region; and a field plate structure disposed over said resurf region ...” Antecedent support for the amendment can be found in the specification in paragraph [0019], lines 6-8, and in paragraph [0020], lines 1-3.

The Examiner contends that elements 9, FP1, and FP2, in Fig. 19, are equivalent to the first plate, second plate, and third plate, respectively, of the field plate structure in claim 1, (Office Action, page 5, lines 4-7). However, as previously pointed out with regard to independent claim 25, Fig. 19 of Fujishima et al. does not show any resurf region below the

alleged field plate structure, as required by independent claim 1. Van Zant and Ghandhi are merely cited to show the epitaxial forming of the semiconductor layer in Fujishima et al., (Office Action, page 5, lines 8-17), but do not disclose teach or suggest any resurf region below a field plate structure.

Since claims 2-13 and 24 are directly or indirectly dependent upon independent claim 1, they are allowable over Fujishima et al. in view of Van Zant and Ghandhi for the same reasons recited above with respect to the allowability of independent claim 1 over Fujishima et al. in view of Van Zant and Ghandhi.

Claims 14-23 were rejected under 35 U.S.C. §103(a) as being unpatentable over Fujishima et al./Van Zant/Ghandhi in view of Noda, U.S. Patent No. 6,617,652, and Ranjan, U.S. Patent No. 5,801,431. Reconsideration of the rejection is respectfully requested.

Since claims 14-23 are directly or indirectly dependent upon independent claim 1, they are allowable over Fujishima et al./Van Zant/Ghandhi for the same reasons recited above with respect to the allowability of independent claim 1 over Fujishima et al./Van Zant/Ghandhi.

Although Noda discloses a high breakdown voltage semiconductor device, (abstract), it nowhere discloses teaches or suggests a field plate structure disposed over a resurf region, as claimed in independent claim 1, and, thus, in dependent claims 14-23. With regard to Ranjan, although it does disclose resurf regions, (see Figs. 5-6), these resurf regions are not disposed below field plate structures, as required in independent claim 1.

Claim 27 was rejected under 35 U.S.C. §103(a) as being unpatentable over Fujishima et al. in view of Noda and Ranjan. Reconsideration of the rejection is respectfully requested.

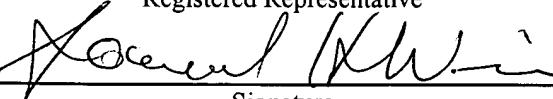
Since dependent claim 27 is indirectly dependent upon independent claim 25, it is allowable over Fujishima et al. for the same reasons recited above with respect to the allowability of independent claim 25 over Fujishima et al. With respect to Noda and Ranjan, neither of them disclose, teach, or suggest a field plate structure disposed over a resurf region, as previously mentioned, the feature of a field plate structure being disposed over a resurf region being required by independent claim 25, and, thus, dependent claim 27.

In view of the foregoing amendments and remarks, allowance of claims 1-29 is respectfully requested.

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Signature

August 8, 2005

Date of Signature

Respectfully submitted,



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